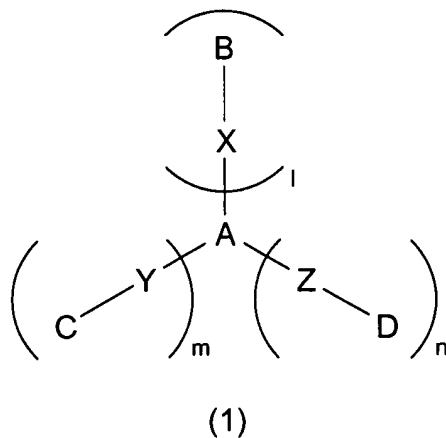


Amendments to the Claims:

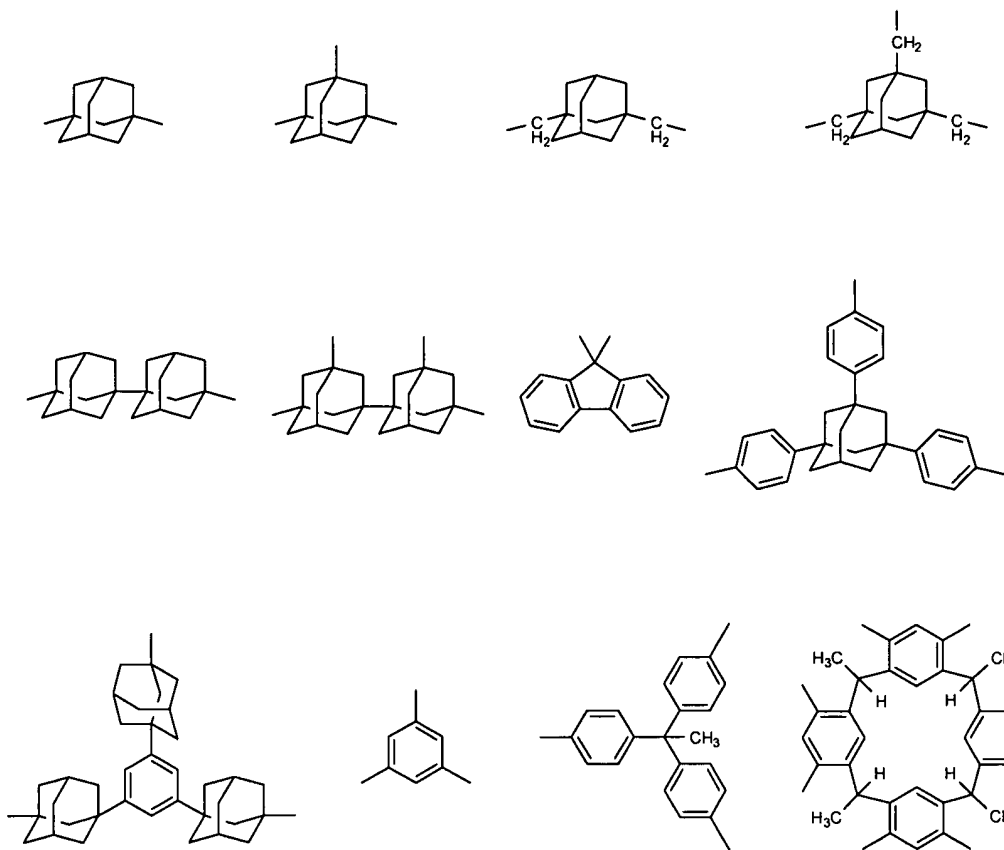
This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of claims:

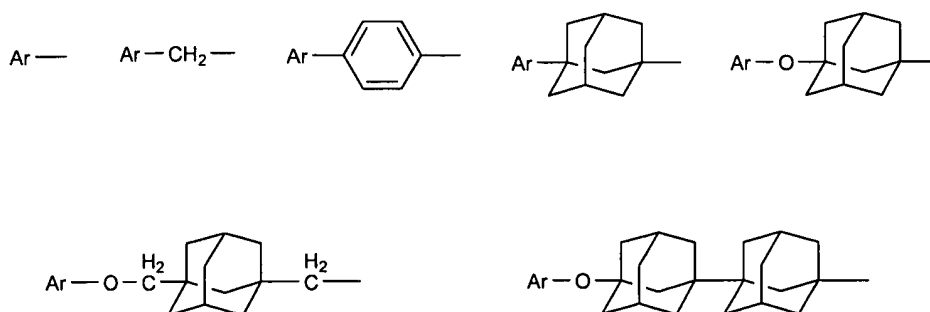
Claim 1 (original): A photoresist base material comprising an extreme ultra-violet reactive organic compound represented by the following general formula (1),



wherein A is an organic group represented by



each of B, C and D is independently an extreme ultra-violet reactive group, a group having reactivity to the action of chromophore active to extreme ultra-violet or an organic group represented by

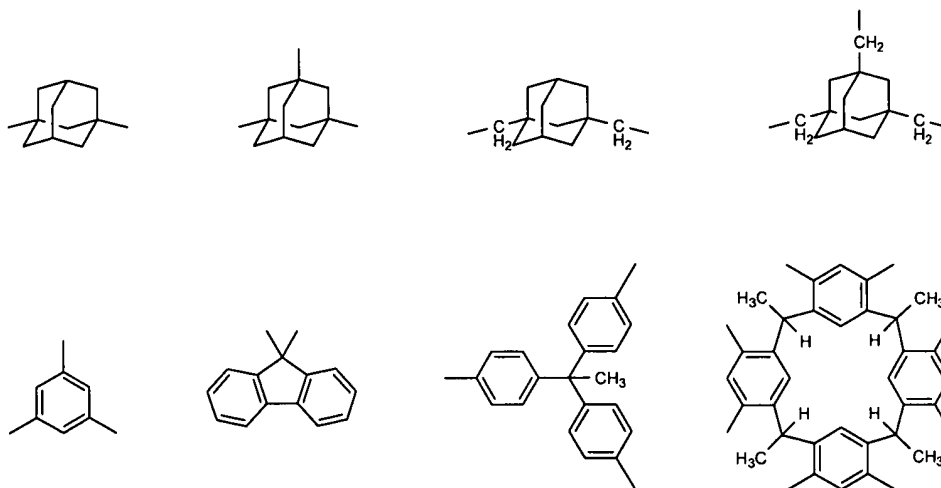


wherein Ar is a phenyl or naphthyl group substituted with RO- and/or ROCO- in which R, RO- and ROCO are extreme ultra-violet reactive groups or groups having reactivity to the action of a chromophore active to extreme ultra-violet,

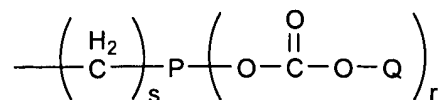
each of X, Y and Z is independently a single bond or an ether bond, and
 $1 + m + n = 2, 3, 4$ or 8.

Claim 2 (original): The photoresist base material as recited in claim 1, wherein said extreme ultra-violet reactive organic compound is in an amorphous state at room temperature and has a molecule whose average diameter is 2 nm or less.

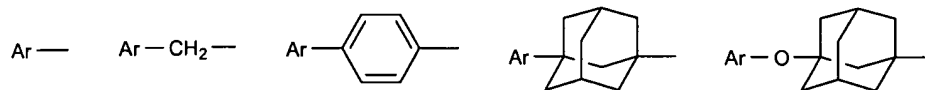
Claim 3 (original): The photoresist base material as recited in claim 1, wherein A is an organic group represented by



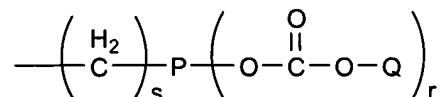
each of B, C and D is a hydrogen atom, tert-butyl, tert-butyloxycarbonylmethyl, tert-butyloxycarbonyl, 1-tetrahydropyranyl, 1-tetrahydrofuranyl, 1-ethoxyethyl, 1-phenoxyethyl, an organic group represented by



in which P is an aromatic group having a valence of $(r + 1)$ and having 6 to 20 carbon atoms, Q is an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10 and s is an integer of 0 to 10,
 or an organic group represented by



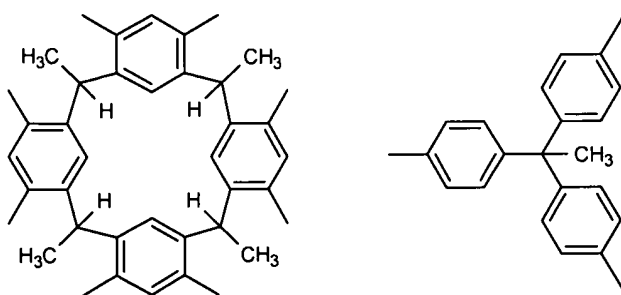
in which Ar is a phenyl or naphthyl group substituted with RO- and/or ROCO- in which R is hydrogen, tert-butyl, tert-butyloxycarbonylmethyl, tert-butyloxycarbonyl, 1-tetrahydropyranyl, 1-tetrahydrofuranyl, 1-ethoxyethyl, 1-phenoxyethyl or an organic group represented by



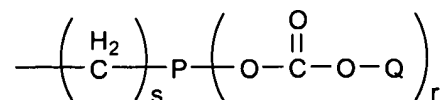
in which P is an aromatic group having a valence of (r + 1) and having 6 to 20 carbon atoms, Q is an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10 and s is an integer of 0 to 10,

and each of X, Y and Z is independently a single bond or an ether bond.

Claim 4 (original): The photoresist base material as recited in claim 3, wherein A is an organic group represented by



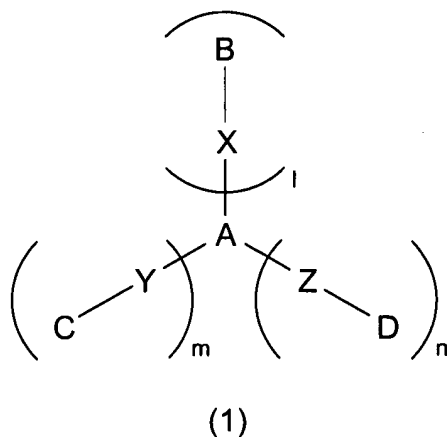
each of B, C and D is a hydrogen atom, tert-butyl, tert-butyloxycarbonylmethyl, tert-butyloxycarbonyl, 1-tetrahydropyranyl, 1-tetrahydrofuranyl, 1-ethoxyethyl, 1-phenoxyethyl or an organic group represented by



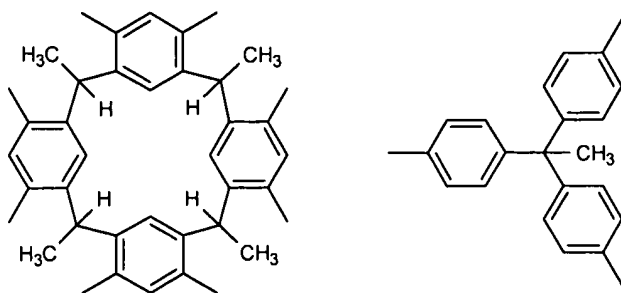
in which P is an aromatic group having a valence of (r + 1) and having 6 to 20 carbon atoms, Q is an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10 and s is an integer of 0 to 10,

and X, Y and Z are ether bonds.

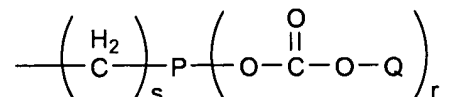
Claim 5 (original): A photoresist base material comprising a radiation-sensitive organic compound represented by the following general formula (1),



wherein A is an organic group represented by



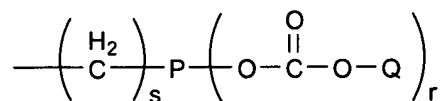
each of B, C and D is independently tert-butyloxycarbonylmethyl, tert-butyloxycarbonyl or an organic group represented by



in which P is an aromatic group having a valence of (r + 1) and having 6 to 20 carbon atoms, Q is an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10 and s is an integer of 0 to 10,

each of X, Y and Z is independently a single bond or an ether bond, and
1 + m + n = 3 or 8.

Claim 6 (original): The photoresist base material as recited in claim 5, wherein the organic group represented by



is 4-(tert-butoxycarbonyloxy)benzyl or 3,5-di(tert-butoxycarbonyloxy)benzyl.

Claim 7 (original): The photoresist base material as recited in claim 5, wherein the radiation is extreme ultra-violet or electron beam.

Claim 8 (currently amended): The photoresist base material as recited in ~~any one of~~ claims 1 to 7 claim 1, wherein at least one of B, C and D is a hydrogen atom and X, Y and Z are ether bonds.

Claim 9 (currently amended): The photoresist base material as recited in ~~any one of 1 to 7~~ claim 1, which has a basic impurity content of 10 ppm or less.

Claim 10 (currently amended): A photoresist composition comprising a solid content containing the photoresist base material recited in ~~any one of claims 1 to 7~~ claim 1 and a solvent.

Claim 11 (original): A photoresist composition comprising a solid content containing the photoresist base material recited in claim 9 and a solvent.

Claim 12 (original): The photoresist composition as recited in claim 10 ~~or 11~~, which further comprises an optically-acid-generating agent.

Claim 13 (original): A method for purification of a photoresist base material, which comprises washing the photoresist base material recited in ~~any one of claims 1 to 7~~ claim 1 with an acidic aqueous solution and treating the material with an ion-exchange resin.

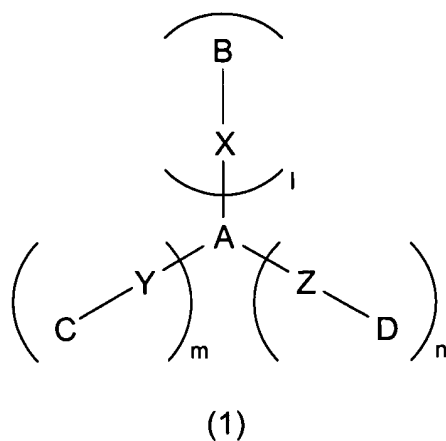
Claim 14 (currently amended): The method for purification of a photoresist base material as recited in claim 13, wherein said acidic aqueous solution is an acetic acid aqueous solution.

Claim 15 (currently amended): A method for improvement of the photoresist base material recited in ~~any one of claims 1 to 7~~ claim 1 in radiation sensitivity, which comprises decreasing the content of basic impurities to 10 ppm or less.

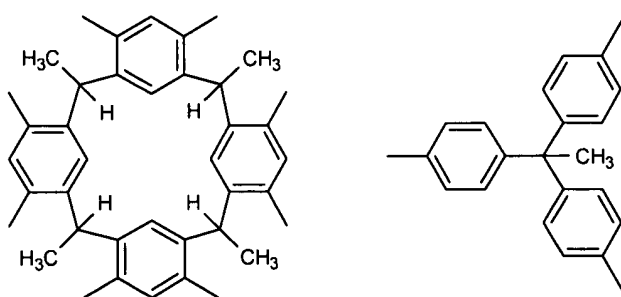
Claim 16 (currently amended): A method for fine processing by lithography, which uses the photoresist composition recited in claim 10 ~~or 11~~.

Claim 17 (currently amended): A semiconductor device fabricated using the photoresist composition recited in claim 10 ~~or 11~~.

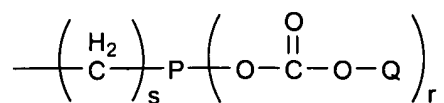
Claim 18 (original): An organic compound represented by the following general formula (1),



wherein A is an organic group represented by



each of B, C and D is independently tert-butyloxycarbonylmethyl, tert-butyloxycarbonyl or an organic group represented by



in which P is an aromatic group having a valence of (r + 1) and having 6 to 20 carbon atoms, Q is an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10 and s is an integer of 0 to 10,

each of X, Y and Z is independently a single bond or an ether bond, and

1 + m + n = 3 or 8.

Claim 19 (original): The organic compound as recited in claim 18, which has a basic impurity content of 10 ppm or less.

Claim 20 (original): A method for purification of an organic compound, which comprises washing the organic compound recited in claim 18 with an acidic aqueous solution and treating the compound with an ion-exchange resin.